List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Thermal analysis of amorphous oxide thin-film transistor degraded by combination of joule heating and hot carrier effect. Applied Physics Letters, 2013, 102, .	1.5	72
2	Analysis of the Temperature Characteristics in Polycrystalline Si Solar Cells Using Modified Equivalent Circuit Model. Japanese Journal of Applied Physics, 2003, 42, 7175-7179.	0.8	70
3	Reversible Oxidation of Graphene Through Ultraviolet/Ozone Treatment and Its Nonthermal Reduction through Ultraviolet Irradiation. Journal of Physical Chemistry C, 2014, 118, 27372-27381.	1.5	66
4	Analysis of thermoelectric properties of amorphous InGaZnO thin film by controlling carrier concentration. AIP Advances, 2015, 5, .	0.6	44
5	Characteristics of Perovskite Solar Cells under Low-Illuminance Conditions. Journal of Physical Chemistry C, 2016, 120, 18986-18990.	1.5	43
6	Low temperature high-mobility InZnO thin-film transistors fabricated by excimer laser annealing. Applied Physics Letters, 2013, 102, .	1.5	41
7	Joule heating effect in nonpolar and bipolar resistive random access memory. Applied Physics Letters, 2015, 107, .	1.5	41
8	Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> double layer antiâ€reflection coating film for crystalline silicon solar cells formed by spray pyrolysis. Energy Science and Engineering, 2016, 4, 269-276.	1.9	36
9	Interface Optoelectronics Engineering for Mechanically Stacked Tandem Solar Cells Based on Perovskite and Silicon. ACS Applied Materials & Interfaces, 2016, 8, 33553-33561.	4.0	36
10	Density of States in Amorphous In-Ga-Zn-O Thin-Film Transistor under Negative Bias Illumination Stress. ECS Journal of Solid State Science and Technology, 2014, 3, Q3001-Q3004.	0.9	34
11	Highly Reliable Polysilsesquioxane Passivation Layer for <i>a</i> -InGaZnO Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Q16-Q19.	0.9	32
12	Effect of contact material on amorphous InGaZnO thin-film transistor characteristics. Japanese Journal of Applied Physics, 2014, 53, 03CC04.	0.8	30
13	Guided filament formation in NiO-resistive random access memory by embedding gold nanoparticles. Applied Physics Letters, 2012, 100, .	1.5	29
14	The Influence of Fluorinated Silicon Nitride Gate Insulator on Positive Bias Stability toward Highly Reliable Amorphous InGaZnO Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Q20-Q23.	0.9	29
15	Effect of Gold Nanoparticle Distribution in TiO2 on the Optical and Electrical Characteristics of Dye-Sensitized Solar Cells. Nanoscale Research Letters, 2017, 12, 513.	3.1	27
16	Flexible Protocrystalline Silicon Solar Cells with Amorphous Buffer Layer. Japanese Journal of Applied Physics, 2006, 45, 6812-6822.	0.8	26
17	Influence of carbon impurities and oxygen vacancies in Al2O3 film on Al2O3/GaN MOS capacitor characteristics. AlP Advances, 2018, 8,	0.6	26
18	Optoelectronic properties of electron beam-deposited NiOx thin films for solar cell application. Results in Physics, 2020, 17, 103122.	2.0	26

#	Article	IF	CITATIONS
19	The influence of sodium ions decorated micro-cracks on the evolution of potential induced degradation in p-type crystalline silicon solar cells. Solar Energy, 2018, 174, 1-6.	2.9	25
20	High-density carrier-accumulated and electrically stable oxide thin-film transistors from ion-gel gate dielectric. Scientific Reports, 2016, 5, 18168.	1.6	24
21	Analysis of electronic structure of amorphous InGaZnO/SiO2interface by angle-resolved X-ray photoelectron spectroscopy. Journal of Applied Physics, 2013, 114, 163713.	1.1	23
22	Impact of Mg level on lattice relaxation in a p-AlGaN hole source layer and attempting excimer laser annealing on p-AlGaN HSL of UVB emitters. Nanotechnology, 2021, 32, 055702.	1.3	23
23	Polycrystalline Silicon Thin Film for Solar Cells Utilizing Aluminum Induced Crystallization Method. Japanese Journal of Applied Physics, 2004, 43, 877-881.	0.8	21
24	Memristive nanoparticles formed using a biotemplate. RSC Advances, 2013, 3, 18044.	1.7	21
25	Highly reliable photosensitive organic-inorganic hybrid passivation layers for <i>a</i> -InGaZnO thin-film transistors. Applied Physics Letters, 2015, 107, .	1.5	21
26	Hot carrier effects in InGaZnO thin-film transistor. Applied Physics Express, 2019, 12, 094007.	1.1	21
27	A novel bifunctional protein supramolecule for construction of carbon nanotube–titanium hybrid material. Chemical Communications, 2011, 47, 12649.	2.2	20
28	Low-temperature fabrication of solution-processed InZnO thin-film transistors with Si impurities by UV/O3-assisted annealing. AIP Advances, 2012, 2, .	0.6	20
29	Comparison between Effects of PECVD-SiO <sub>x</sub> and Thermal ALD-AlO <sub>x</sub> Passivation Layers on Characteristics of Amorphous InGaZnO TFTs. ECS Journal of Solid State Science and Technology, 2015, 4, Q61-Q65.	0.9	20
30	Effect of excimer laser annealing on <i>a</i> -InGaZnO thin-film transistors passivated by solution-processed hybrid passivation layers. Journal Physics D: Applied Physics, 2016, 49, 035102.	1.3	20
31	Significant mobility improvement of amorphous In-Ga-Zn-O thin-film transistors annealed in a low temperature wet ambient environment. Applied Physics Letters, 2018, 112, 193501.	1.5	20
32	Characterizations of Al <sub>2</sub> O <sub>3</sub> gate dielectric deposited on nâ€GaN by plasmaâ€assisted atomic layer deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1426-1429.	0.8	19
33	Fabrication of perovskite solar cells using sputter-processed CH <sub>3</sub> NH <sub>3</sub> Pbl <sub>3</sub> films. Applied Physics Express, 2017, 10, 094101.	1.1	19
34	Air-stable perovskite photovoltaic cells with low temperature deposited NiOx as an efficient hole-transporting material. Optical Materials Express, 2020, 10, 1801.	1.6	19
35	Low temperature cured poly-siloxane passivation for highly reliable <i>a</i> -InGaZnO thin-film transistors. Applied Physics Letters, 2018, 112,	1.5	18
36	Effects of grain boundaries in polycrystalline silicon thin-film solar cells based on the two-dimensional model. Solar Energy Materials and Solar Cells, 2001, 65, 201-209.	3.0	17

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#	Article	IF	CITATIONS
37	Reliability Improvement of Amorphous InGaZnO Thin-Film Transistors by Less Hydroxyl-Groups Siloxane Passivation. Journal of Display Technology, 2016, 12, 263-267.	1.3	17
38	High-Performance Fully Solution-Processed Oxide Thin-Film Transistors via Photo-Assisted Role Tuning of InZnO. ACS Applied Electronic Materials, 2020, 2, 2398-2407.	2.0	17
39	Fabrication of Nanoshell-Based 3D Periodic Structures by Templating Process using Solution-derived ZnO. Nanoscale Research Letters, 2017, 12, 419.	3.1	16
40	Enhanced Thermoelectric Transport and Stability in Atomic Layer Deposited-HfO <sub>2</sub> /ZnO and TiO <sub>2</sub> /ZnO-Sandwiched Multilayer Thin Films. ACS Applied Materials & Interfaces, 2020, 12, 49210-49218.	4.0	16
41	Unique Phenomenon in Degradation of Amorphous In\$_{2}\$O\$_{3}\$–Ga\$_{2}\$O\$_{3}\$–ZnO Thin-Film Transistors under Dynamic Stress. Applied Physics Express, 2011, 4, 104103.	1.1	15
42	Biological Construction of Singleâ€Walled Carbon Nanotube Electron Transfer Pathways in Dye‣ensitized Solar Cells. ChemSusChem, 2014, 7, 2805-2810.	3.6	15
43	Hierarchical core–shell heterostructure of H <sub>2</sub> O-oxidized ZnO nanorod@Mg-doped ZnO nanoparticle for solar cell applications. Materials Advances, 2020, 1, 1253-1261.	2.6	15
44	Elucidating the mechanism of potential induced degradation delay effect by ultraviolet light irradiation for p-type crystalline silicon solar cells. Solar Energy, 2020, 199, 55-62.	2.9	15
45	Crystallization to polycrystalline silicon thin film and simultaneous inactivation of electrical defects by underwater laser annealing. Applied Physics Letters, 2012, 101, 252106.	1.5	14
46	Thermal reversibility in electrical characteristics of ultraviolet/ozone-treated graphene. Applied Physics Letters, 2013, 103, 063107.	1.5	14
47	H and Au diffusion in high mobility <i>a</i> -InGaZnO thin-film transistors via low temperature KrF excimer laser annealing. Applied Physics Letters, 2017, 110, .	1.5	14
48	Metal-nanoparticle-induced crystallization of amorphous Ge film using ferritin. Applied Surface Science, 2012, 258, 3410-3414.	3.1	13
49	Thermal analysis for observing conductive filaments in amorphous InGaZnO thin film resistive switching memory. Applied Physics Letters, 2014, 105, 123506.	1.5	13
50	High performance top gate a-IGZO TFT utilizing siloxane hybrid material as a gate insulator. AIP Advances, 2018, 8, .	0.6	13
51	Segregation-free bromine-doped perovskite solar cells for IoT applications. RSC Advances, 2019, 9, 32833-32838.	1.7	13
52	Unique degradation under AC stress in high-mobility amorphous In–W–Zn–O thin-film transistors. Applied Physics Express, 2020, 13, 054003.	1.1	13
53	Analysis of printed silver electrode on amorphous indium gallium zinc oxide. Japanese Journal of Applied Physics, 2014, 53, 04EB03.	0.8	12
54	Creating Reversible p–n Junction on Graphene through Ferritin Adsorption. ACS Applied Materials & Interfaces, 2016, 8, 8192-8200.	4.0	12

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55	Instantaneous Semiconductor-to-Conductor Transformation of a Transparent Oxide Semiconductor a-InGaZnO at 45 °C. ACS Applied Materials & Interfaces, 2018, 10, 24590-24597.	4.0	12
56	Improvement in Bias Stress Stability of Solution-Processed Amorphous InZnO Thin-Film Transistors via Low-Temperature Photosensitive Passivation. IEEE Electron Device Letters, 2020, 41, 1372-1375.	2.2	12
57	Crystallization of amorphous Ge thin film using Cu nanoparticle synthesized and delivered by ferritin. Journal of Crystal Growth, 2013, 382, 31-35.	0.7	11
58	Thermo-stable carbon nanotube-TiO2nanocompsite as electron highways in dye-sensitized solar cell produced by bio-nano-process. Nanotechnology, 2015, 26, 285601.	1.3	11
59	Reactivity and stability of thallium oxide for fabricating TlSnZnO toward thin-film transistors with high mobility. Journal of Alloys and Compounds, 2016, 672, 413-418.	2.8	11
60	Fluorine incorporation in solution-processed poly-siloxane passivation for highly reliable <i>a</i> -InGaZnO thin-film transistors. Journal Physics D: Applied Physics, 2018, 51, 125105.	1.3	11
61	Dimethylaluminum hydride for atomic layer deposition of Al <sub>2</sub> O <sub>3</sub> passivation for amorphous InGaZnO thin-film transistors. Applied Physics Express, 2018, 11, 061103.	1.1	11
62	Optimizing the thermoelectric performance of InGaZnO thin films depending on crystallinity via hydrogen incorporation. Applied Surface Science, 2020, 527, 146791.	3.1	11
63	Analysis of Device Performance by Quasi Three-Dimensional Simulation for Thin Film Polycrystalline Silicon Solar Cells with Columnar Structure. Japanese Journal of Applied Physics, 2001, 40, 6783-6787.	0.8	10
64	Effects of Gate Insulator on Thin-Film Transistors With ZnO Channel Layer Deposited by Plasma-Assisted Atomic Layer Deposition. Journal of Display Technology, 2013, 9, 694-698.	1.3	10
65	Control of verticality and (111) orientation of In-catalyzed silicon nanowires grown in the vapour–liquid–solid mode for nanoscale device applications. Journal of Materials Chemistry C, 2015, 3, 11577-11580.	2.7	10
66	Nano-crystallization in ZnO-doped In2O3 thin films via excimer laser annealing for thin-film transistors. AIP Advances, 2016, 6, 065216.	0.6	10
67	Recover possibilities of potential induced degradation caused by the microâ€cracked locations in pâ€type crystalline silicon solar cells. Progress in Photovoltaics: Research and Applications, 2021, 29, 423-432.	4.4	10
68	Thermal distribution in amorphous InSnZnO thinâ€film transistor. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1561-1564.	0.8	9
69	Vapor-Induced Improvements in Field Effect Mobility of Transparent a-IGZO TFTs. ECS Journal of Solid State Science and Technology, 2014, 3, Q3050-Q3053.	0.9	9
70	Effect of inversion layer at iron pyrite surface on photovoltaic device. Japanese Journal of Applied Physics, 2018, 57, 032301.	0.8	9
71	Structural study of NiOx thin films fabricated by radio frequency sputtering at low temperature. Thin Solid Films, 2018, 646, 209-215.	0.8	9
72	Self-Heating Suppressed Structure of a-IGZO Thin-Film Transistor. IEEE Electron Device Letters, 2018, 39, 1322-1325.	2.2	9

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73	Degradation phenomenon in metal-oxide-semiconductor thin-film transistors and techniques for its reliability evaluation and suppression. Japanese Journal of Applied Physics, 2019, 58, 090502.	0.8	9
74	Numerical analysis of bulk diffusion length in thin-film c-Si solar cells. Solar Energy Materials and Solar Cells, 2003, 75, 433-438.	3.0	8
75	Nucleation Control by Intermittent Supply of Dichlorosilane towards the Fabrication of Polycrystalline Silicon Thin Films with Large Grain Size. Japanese Journal of Applied Physics, 2003, 42, 6759-6765.	0.8	8
76	Three-Dimensional Nanodot-Type Floating Gate Memory Fabricated by Bio-Layer-by-Layer Method. Applied Physics Express, 2011, 4, 085004.	1.1	8
77	Highly reliable low-temperature (180 °C) solution-processed passivation for amorphous In–Zn–O thin-film transistors. Applied Physics Express, 2019, 12, 064002.	1.1	8
78	Evaluate Fixed Charge and Oxideâ€Trapped Charge on SiO <sub>2</sub> /GaN Metalâ€Oxideâ€Semiconductor Structure Before and After Postannealing. Physica Status Solidi (B): Basic Research, 2020, 257, 1900444.	0.7	8
79	Development of High-Reliability and -Stability Chemical Sensors Based on an Extended-Gate Type Amorphous Oxide Semiconductor Thin-Film Transistor. ACS Applied Electronic Materials, 2020, 2, 405-408.	2.0	8
80	Low-Temperature-Processed Zinc Oxide Thin-Film Transistors Fabricated by Plasma-Assisted Atomic Layer Deposition. Japanese Journal of Applied Physics, 2012, 51, 02BF04.	0.8	8
81	Low-Operating-Voltage Solution-Processed InZnO Thin-Film Transistors Using High-k SrTa <sub>2</sub> 0 <sub>6</sub> . Japanese Journal of Applied Physics, 2012, 51, 03CB05.	0.8	7
82	Fabrication of Zinc Oxide Nanopatterns by Quick Gel-Nanoimprint Process toward Optical Switching Devices. Japanese Journal of Applied Physics, 2013, 52, 03BA02.	0.8	7
83	Floating gate memory with charge storage dots array formed by Dps protein modified with site-specific binding peptides. Nanotechnology, 2015, 26, 195201.	1.3	7
84	Ultra-short channel junctionless transistor with a one-dimensional nanodot array floating gate. Applied Physics Letters, 2015, 106, .	1.5	7
85	Investigation of crystallinity and planar defects in the Si nanowires grown by vapor–liquid–solid mode using indium catalyst for solar cell applications. Japanese Journal of Applied Physics, 2016, 55, 01AE03.	0.8	7
86	Self-heating induced instability of oxide thin film transistors under dynamic stress. Applied Physics Letters, 2016, 108, .	1.5	7
87	Improvement of Thermoelectric Properties of a-InGaZnO Thin Film by Optimizing Carrier Concentration. Journal of Electronic Materials, 2016, 45, 1377-1381.	1.0	7
88	30â€3: High Performance All Solution Processed Oxide Thinâ€Film Transistor via Photoâ€induced Semiconductorâ€to onductor Transformation of aâ€inZnO. Digest of Technical Papers SID International Symposium, 2019, 50, 422-425.	0.1	7
89	The optical properties of silicon-rich silicon nitride prepared by plasma-enhanced chemical vapor deposition. Materials Science in Semiconductor Processing, 2019, 90, 54-58.	1.9	7
90	Extension of the {100}-Oriented Grain-Boundary Free Si Thin Film Grown by a Continuous-Wave Laser Lateral Crystallization. Thin Solid Films, 2020, 708, 138127.	0.8	7

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91	Crystallographic analysis of high quality poly-Si thin films deposited by atmospheric pressure chemical vapor deposition. Solar Energy Materials and Solar Cells, 2002, 74, 255-260.	3.0	6
92	Fabrication and Characterization of Triple-junction Amorphous Silicon Based Solar Cell with Nanocrystalline Silicon Bottom Cell. , 2006, , .		6
93	Polycrystalline silicon thin-film transistor utilizing self-assembled monolayer for crystallization. Thin Solid Films, 2013, 540, 266-270.	0.8	6
94	Highly reliable passivation layer for a-InGaZnO thin-film transistors fabricated using polysilsesquioxane. Materials Research Society Symposia Proceedings, 2014, 1633, 139-144.	0.1	6
95	Silica-sol-based spin-coating barrier layer against phosphorous diffusion for crystalline silicon solar cells. Nanoscale Research Letters, 2014, 9, 659.	3.1	6
96	Effect of Fluorine in a Gate Insulator on the Reliability of Indium-Gallium-Zinc Oxide Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2016, 5, N17-N21.	0.9	6
97	Theoretical investigation about the optical characterization of coneâ€shaped pinâ€Si nanowire for top cell application. Energy Science and Engineering, 2016, 4, 383-393.	1.9	6
98	Biotemplated Synthesis of TiO <sub>2</sub> -Coated Gold Nanowire for Perovskite Solar Cells. ACS Omega, 2017, 2, 5478-5485.	1.6	6
99	Carrier dynamics in the potential-induced degradation in single-crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 08RG14.	0.8	6
100	Easy and green preparation of a graphene–TiO <sub>2</sub> nanohybrid using a supramolecular biomaterial consisting of artificially bifunctionalized proteins and its application for a perovskite solar cell. Nanoscale, 2018, 10, 19249-19253.	2.8	6
101	Bias stress and humidity exposure of amorphous InGaZnO thin-film transistors with atomic layer deposited Al2O3 passivation using dimethylaluminum hydride at 200 °C. Journal Physics D: Applied Physics, 2020, 53, 165103.	1.3	6
102	Sterically controlled docking of gold nanoparticles on ferritin surface by DNA hybridization. Nanotechnology, 2011, 22, 275312.	1.3	5
103	Low-Temperature-Processed Zinc Oxide Thin-Film Transistors Fabricated by Plasma-Assisted Atomic Layer Deposition. Japanese Journal of Applied Physics, 2012, 51, 02BF04.	0.8	5
104	Fabrication of nano-patterns using quick gel-nanoimprint process. , 2012, , .		5
105	Highly stable dye-sensitized solar cells with quasi-solid-state electrolyte based on Flemion. Solar Energy, 2014, 110, 648-655.	2.9	5
106	Selection of a novel peptide aptamer with high affinity for TiO2-nanoparticle through a direct electroporation with TiO2-binding phage complexes. Journal of Bioscience and Bioengineering, 2016, 122, 528-532.	1.1	5
107	Growth and characterization of low composition Ge, <i>x</i> in epi-Si <sub>1â^'<i>x</i> </sub> Ge <i>x</i> ( <i>x</i> ⩽  10%) active layer for fabrication of hydrogenated bottom s Journal Physics D: Applied Physics, 2018, 51, 185107.	olarscell.	5
108	Rapid photo-assisted activation and enhancement of solution-processed InZnO thin-film transistors. Journal Physics D: Applied Physics, 2020, 53, 045102.	1.3	5

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109	High Performance Amorphous In–Ga–Zn–O Thin-Film Transistors with Low Temperature High-k Solution Processed Hybrid Gate Insulator. ECS Journal of Solid State Science and Technology, 2020, 9, 025002.	0.9	5
110	Optimum Designing of Single Crystalline Silicon Thin Film Solar Cells with Graded Active Layer. Japanese Journal of Applied Physics, 2001, 40, 6778-6782.	0.8	4
111	Light trapping effect of nanoimprinted-textured crystalline silicon solar cells. , 2013, , .		4
112	Numerical analysis of monocrystalline silicon solar cells with fine nanoimprinted textured surface. Japanese Journal of Applied Physics, 2017, 56, 022301.	0.8	4
113	Growth of InGaZnO nanowires via a Mo/Au catalyst from amorphous thin film. Applied Physics Letters, 2017, 111, 033104.	1.5	4
114	SrTa2O6 induced low voltage operation of InGaZnO thin-film transistors. Thin Solid Films, 2018, 665, 173-178.	0.8	4
115	Effective minority carrier lifetime as an indicator for potential-induced degradation in p-type single-crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2019, 58, 106507.	0.8	4
116	Physical and electrical properties of ALD-Al <sub>2</sub> O <sub>3</sub> /GaN MOS capacitor annealed with high pressure water vapor. Japanese Journal of Applied Physics, 2019, 58, 040902.	0.8	4
117	Evaluation of Recombination Velocity at Grain Boundaries in Poly-Si Solar Cells with Laser Beam Induced Current. Solid State Phenomena, 2003, 93, 351-354.	0.3	3
118	Effects of Si and Ti impurities on electrical properties of sol–gel-derived amorphous SrTa2O6 thin films by UV/O3 treatment. Applied Physics A: Materials Science and Processing, 2013, 112, 425-430.	1.1	3
119	A distance-controlled nanoparticle array using PEGylated ferritin. Materials Research Express, 2014, 1, 045410.	0.8	3
120	Photomechanical modification of ZnS microcrystal to enhance electroluminescence by ultrashort-pulse laser processing. Applied Physics Express, 2017, 10, 021201.	1.1	3
121	Solution-derived SiO <sub>2</sub> gate insulator formed by CO <sub>2</sub> laser annealing for polycrystalline silicon thin-film transistors. Japanese Journal of Applied Physics, 2017, 56, 056503.	0.8	3
122	Alterations in ambipolar characteristic of graphene due to adsorption ofEscherichia colibacteria. Journal Physics D: Applied Physics, 2018, 51, 115102.	1.3	3
123	Improvement of Amorphous InGaZnO Thinâ€Film Transistor Using Highâ€k SrTa <sub>2</sub> O <sub>6</sub> as Gate Insulator Deposited by Sputtering Method. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700773.	0.8	3
124	Thermally Stimulated Current Analysis of Defects in Sol–Gel Derived SrTa\$_{2}\$O\$_{6}\$ Thin-Film Capacitors. Japanese Journal of Applied Physics, 2012, 51, 09LA18.	0.8	2
125	Construction of Au nanoparticle/ferritin satellite nanostructure. Chemical Physics Letters, 2012, 547, 52-57.	1.2	2
126	Analysis of electron traps in SiO <inf>2</inf> /IGZO interface by cyclic capacitance-voltage method. ,		2

2012, , .

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127	Plasmon Absorbance of SiO <sub>2</sub> -Wrapped Gold Nanoparticles Selectively Coupled with Ti Substrate Using Porter Protein. Japanese Journal of Applied Physics, 2013, 52, 125201.	0.8	2
128	High-mobility material research for thin-film transistor with amorphous thallium–zinc–tin oxide semiconductor. Japanese Journal of Applied Physics, 2015, 54, 104101.	0.8	2
129	Potential of perovskite solar cells for power sources of IoT applications. , 2016, , .		2
130	Low surface reflectance by nanoimprinted texture with silicon-rich silicon nitride layer. Journal Physics D: Applied Physics, 2017, 50, 455108.	1.3	2
131	One-dimensional array of gold nanoparticles fabricated using biotemplate and its application to fine FET. Japanese Journal of Applied Physics, 2018, 57, 06HC05.	0.8	2
132	Photosensitive polysiloxane passivation fabricated at low temperature for highly reliable amorphous InGaZnO thin-film transistors. Japanese Journal of Applied Physics, 2018, 57, 090306.	0.8	2
133	Transient carrier recombination dynamics in potentialâ€induced degradation pâ€type singleâ€crystalline Si photovoltaic modules. Progress in Photovoltaics: Research and Applications, 2019, 27, 682-692.	4.4	2
134	Thin-Film Devices Fabricated on Double-Layered Polycrystalline Silicon Films Formed by Green Laser Annealing. Japanese Journal of Applied Physics, 2012, 51, 03CA03.	0.8	2
135	Thermally Stimulated Current Analysis of Defects in Sol–Gel Derived SrTa2O6Thin-Film Capacitors. Japanese Journal of Applied Physics, 2012, 51, 09LA18.	0.8	2
136	Optical and Electrical Transport Evaluations of n-Type Iron Pyrite Single Crystals. ACS Omega, 2021, 6, 31358-31365.	1.6	2
137	Evaluation of annual performance for buildingâ€integrated photovoltaics based on 2â€ŧerminal perovskite/silicon tandem cells under realistic conditions. Energy Science and Engineering, 2022, 10, 1373-1383.	1.9	2
138	Effects of hydrogen dilution grading in active layer on performance of nanocrystalline single junction bottom component and corresponding a-Si:H based triple junction solar cells. , 2006, , .		1
139	Thin-Film Devices Fabricated on Double-Layered Polycrystalline Silicon Films Formed by Green Laser Annealing. Japanese Journal of Applied Physics, 2012, 51, 03CA03.	0.8	1
140	Analysis of Electron Traps in a-IGZO Thin Films after High Pressure Vapor Annealing by Capacitance–Voltage Method. Materials Research Society Symposia Proceedings, 2012, 1436, 1.	0.1	1
141	Dependence of semiconductor nanoparticle size on spray condition in electro-spray deposition method. , 2012, , .		1
142	Impact of Underwater Laser Annealing on Polycrystalline Silicon Thin-Film Transistor for Inactivation of Electrical Defects at Super Low Temperature. Journal of Display Technology, 2013, 9, 741-746.	1.3	1
143	Reliability of bottom gate amorphous InGaZnO thin-film transistors with siloxane passivation layer. , 2014, , .		1
144	Development of solution-derived diffusion barrier layer for back-contact crystalline silicon solar		1

cell., 2014, , .

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145	Evaluation of band structure and conductive property of iron pyrite (FeS <inf>2</inf> ) thin film deposited by spin-coating. , 2015, , .		1
146	Removing process of the three-dimension periodic nanostructure fabricated from KMPR photoresist. Japanese Journal of Applied Physics, 2019, 58, SDDF08.	0.8	1
147	Low Temperature High-k Solution Processed Hybrid Gate Insulator for High Performance Amorphous In-Ga-Zn-O Thin-Film Transistors. , 2019, , .		1
148	Improvement of the stability of an electric double-layer transistor using a 1H,1H,2H,2H-perfluorodecyltriethoxysilane barrier layer. Japanese Journal of Applied Physics, 2019, 58, 040907.	0.8	1
149	Influence of UV light on the increase of SiNx conductivity toward elucidation of potential induced degradation mechanism. , 2019, , .		1
150	Pâ€11: High Performance Allâ€Solution Processed InZnO Thinâ€Film Transistors via Photoâ€Functionalization at Varying Fluence and Annealing Environment. Digest of Technical Papers SID International Symposium, 2020, 51, 1350-1353.	0.1	1
151	Biotemplates and Their Application to Electronic Devices. , 2016, , 119-143.		1
152	Photo-assisted Processing of Amorphous Gallium Oxide (a-GaOx) Thin Film for Flexible and Transparent Device Application. , 2020, , .		1
153	DC Bias Effect on Nanocrystalline Silicon Solar Cell Deposited under a High Power High Pressure Regime. , 2006, , .		0
154	Effect of ZnO deposition condition for back reflector on the performance of nano-crystalline silicon solar cell. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	0
155	Low temperature processed ZnO thin film transistors fabricated by plasma assisted atomic layer deposition. , 2011, , .		0
156	Fabrication of PbTiO <inf>3</inf> and Pt self-organized nanocrystal array structure on atomically flat sapphire. , 2011, , .		0
157	Characteristics of solution-processed TFTs with In <inf>4</inf> ZnO <inf>x</inf> /SrTa <inf>2</inf> O <inf>6</inf> thin films. , 2011, , .		0
158	Impact of atomization treatment on ZnS phosphor for inorganic EL. , 2011, , .		0
159	Low-temperature crystallization of amorphous Ge thin films using metal nanoparticles. , 2011, , .		0
160	Application of endohedral iron-oxide ferritin to resistive memory. , 2011, , .		0
161	Preparation of ZnO thin films by plasma-assisted atomic layer deposition for the application to thin film transistors. , 2011, , .		0
162	Fabrication of semiconductor nanoparticles using electro spray deposition method. , 2011, , .		0

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163	Thin film transistors and photo diodes fabricated on double-layered polycrystalline silicon films formed by green laser annealing. , 2011, , .		0
164	Size Control of ZnS Nanoparticles by Electro-Spray Deposition Method. Japanese Journal of Applied Physics, 2012, 51, 03CC02.	0.8	0
165	Crystallization Using Biomineralized Nickel Nanodots of Amorphous Silicon Thick Films Deposited by Chemical Vapor Deposition, Sputtering and Electron Beam Evaporation. Japanese Journal of Applied Physics, 2012, 51, 03CA01.	0.8	0
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